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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known Application Number 10/054601 Filing Date January 22, 2002 First Named Inventor Forbes, Leonard Group Art Unit 2879 Examiner Name Santiago, Mariceli	
		Attorney Docket No: 303.504US3	

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T ²

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Mariceli Santiago

DATE CONSIDERED

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Sheet 1 of 2

Form 1449* INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No.: 303.504US3	Serial No. Unknown
	S-10051601 01/22/02	
	Applicant: Leonard Forbes et al.	Filing Date: Herewith
Group: Unknown		

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Sheet 2 of 2

Form 1449*	Atty. Docket No.: 303.504US3	Serial No. <u>Unknown</u> 10/054601
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Applicant: Leonard Forbes et al.	
	Filing Date: Herewith	Group: <u>Unknown</u> 2879

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<i>fw</i>	Huq, S.E., et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters", <u>9th International Vacuum Microelectronics Conference</u> , St. Petersburg, pp. 367-370, (1996) <i>no month</i>
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